Supporting Information for

Thickness-Dependent Bandgap Tunable Molybdenum Disulfide Films for Optoelectronics

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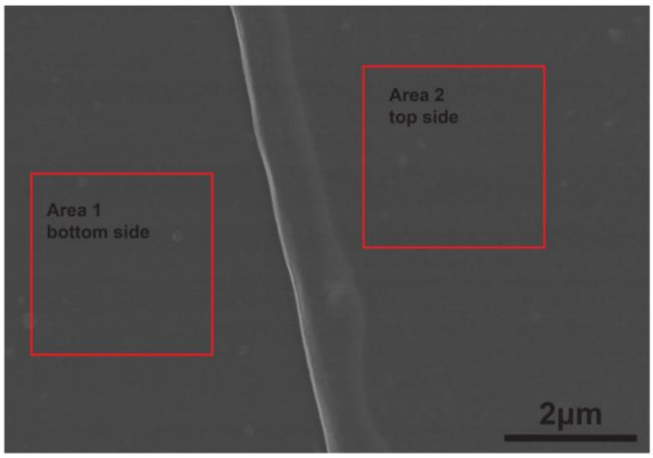

Figure S1. SEM image of bottom (left) and top (right) sides of 50 nm MoS_2 film after peeled off on the left part by tape.

	element	Top side	Bottom side
Atomic %	Mo-L	31.71	33.86
	S-K	68.29	66.14

Table S1. EDAX of bottom (left) and top (right) sides of 50 nm MoS_2 film after peeled off on the left part by tape.

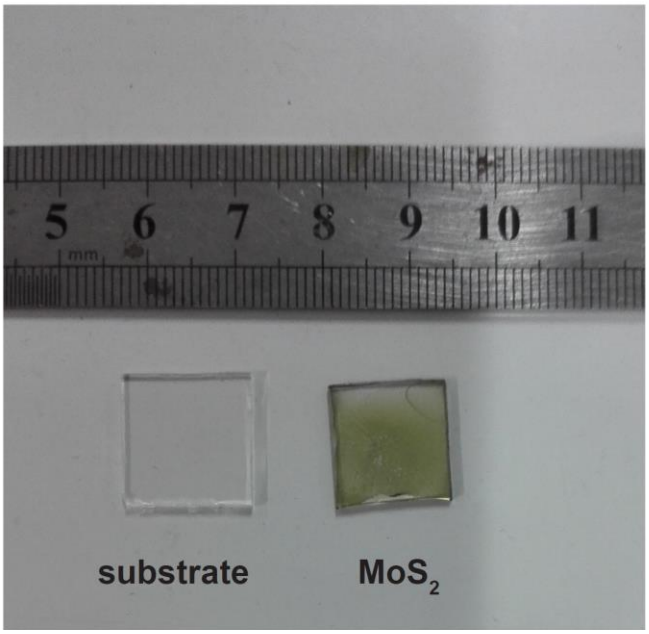

Figure S2. A large area photograph of MoS_2 film, the left is the quartz substrate and the right is MoS_2 film prepared on quartz.

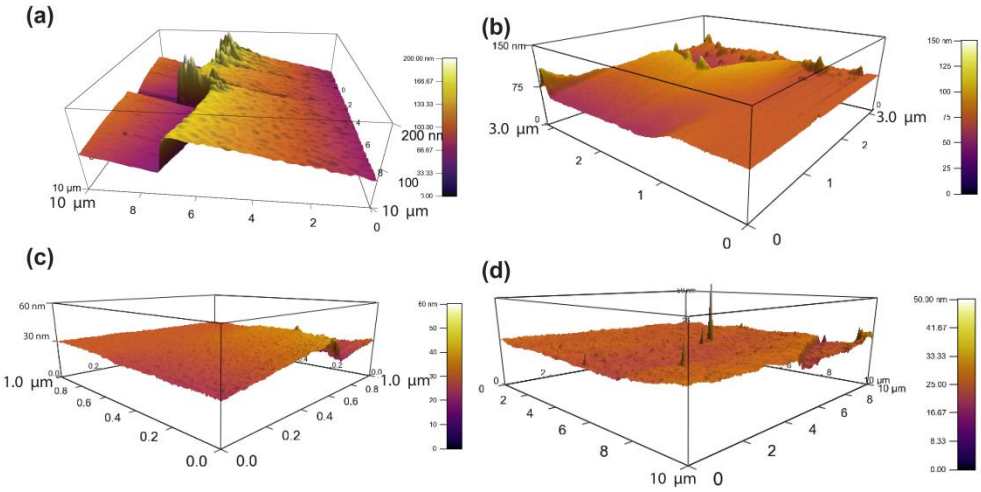

Figure S3. Perspective view of AFM images collected from MoS_2 films produced from Mo precursor concentration of 200 mM (a), 150 mM (b), 50 mM (c) and 13 mM (d), respectively.